Substitute Form PTO-1449 (Modified)

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Application No. 10/724,005

Information Disclosure Statement by Applicant (Use several sheets if necessary) Applicant Alexei A. Erchak

Filing Date

Group Art Unit 2811

(37 CFR §1.98(b))

November 26, 2003

U.S. Patent Documents								
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate	
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EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.					

Substitute Form PTO-144 Patent and Trademark Office

Information Disclosure Statement
by Applicant
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Applicant
Alexei A. Erchak

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